74AUP2G00

Low-power dual 2-input NAND gate Rev. 7 — 8 June 2012

Product data sheet

General description 1.

The 74AUP2G00 provides dual 2-input NAND function.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1 000 V
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G00DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74AUP2G00GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1
74AUP2G00GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm	SOT1089
74AUP2G00GD	–40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3\times2\times0.5$ mm	SOT996-2
74AUP2G00GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 \times 1.6 \times 0.5 mm	SOT902-2
74AUP2G00GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 \times 1.0 \times 0.35 mm	SOT1116
74AUP2G00GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1.0 \times 0.35 mm	SOT1203

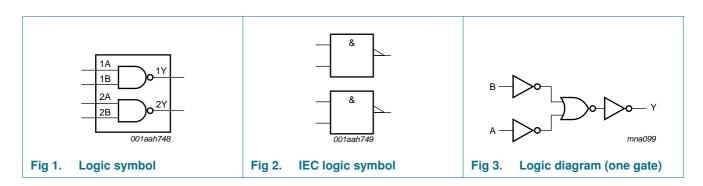
4. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74AUP2G00DC	p00
74AUP2G00GT	p00
74AUP2G00GF	pA
74AUP2G00GD	p00
74AUP2G00GM	p00
74AUP2G00GN	pA
74AUP2G00GS	pA

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



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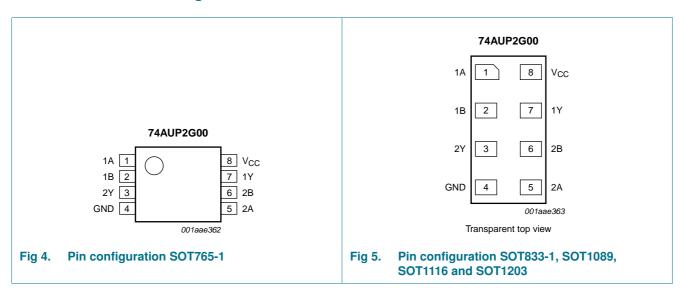
74AUP2G00 NXP Semiconductors

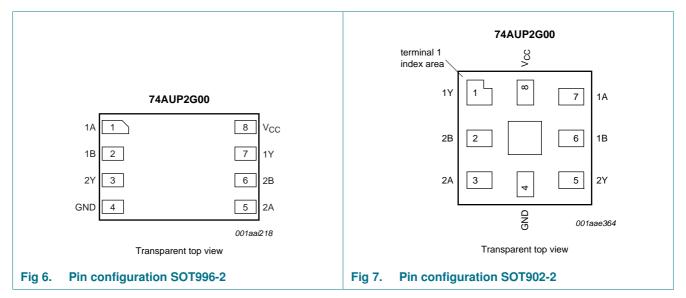
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Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

74AUP2G00

Symbol	Pin	Pin				
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2				
1A, 2A	1, 5	7, 3	data input			
1B, 2B	2, 6	6, 2	data input			
GND	4	4	ground (0 V)			
1Y, 2Y	7, 3	1, 5	data output			
V _{CC}	8	8	supply voltage			

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7. Functional description

Table 4. Function table[1]

Input	Output	
nA	nB	nY
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

^[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	$V_I < 0 V$	– 50	-	mA
V_{I}	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
V_{O}	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±20	mA
I _{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		8.0	3.6	V
VI	input voltage		0	3.6	V
V _O	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	200	ns/V

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^[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly at 8.0 mW/K.
For XSON8, XSON8U and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly at 7.8 mW/K.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

$ \begin{array}{llllllllllllllllllllllllllllllllllll$	C	- - - 0.30 × V _{CC} 0.35 × V _{CC} 0.7 0.9	V V V
$\begin{array}{c} V_{CC} = 0.9 \ V \ to \ 1.95 \ V \\ V_{CC} = 2.3 \ V \ to \ 2.7 \ V \\ V_{CC} = 3.0 \ V \ to \ 3.6 \ V \\ V_{CC} = 3.0 \ V \ to \ 3.6 \ V \\ V_{CC} = 0.8 \ V \\ V_{CC} = 0.9 \ V \ to \ 1.95 \ V \\ V_{CC} = 2.3 \ V \ to \ 2.0 \\ \hline \\ V_{CC} = 2.3 \ V \ to \ 2.0 \\ \hline \\ V_{CC} = 2.3 \ V \ to \ 1.95 \ V \\ V_{CC} = 2.3 \ V \ to \ 3.6 \ V \\ V_{CC} = 2.3 \ V \ to \ 3.6 \ V \\ V_{CC} = 3.0 \ V \ to \ 3.6 \ V \\ V_{CC} = 3.0 \ V \ to \ 3.6 \ V \\ V_{CC} = 3.0 \ V \ to \ 3.6 \ V \\ V_{CC} = 0.1 \ MA; \ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \\ V_{CC} = 0.1 \ V_{CC} = 0.1 \ V_{CC} = 0.1 \\ \hline \\ I_{O} = -1.1 \ mA; \ V_{CC} = 1.1 \ V \\ I_{O} = -1.7 \ mA; \ V_{CC} = 1.65 \ V \\ I_{O} = -2.7 \ mA; \ V_{CC} = 2.3 \ V \\ I_{O} = -2.7 \ mA; \ V_{CC} = 3.0 \ V \\ I_{O} = -4.0 \ mA; \ V_{CC} = 3.0 \ V \\ V_{CC} = 3.0 \ V \\ I_{O} = 20 \ \mu A; \ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \\ I_{O} = 1.1 \ mA; \ V_{CC} = 1.4 \ V \\ I_{O} = 1.7 \ mA; \ V_{CC} = 1.4 \ V \\ I_{O} = 1.7 \ mA; \ V_{CC} = 1.4 \ V \\ I_{O} = 1.9 \ mA; \ V_{CC} = 1.65 \ V \\ I_{O$	C	- 0.30 × V _{CC} 0.35 × V _{CC} 0.7 0.9	V V V V V V V V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	- - - -	- 0.30 × V _{CC} 0.35 × V _{CC} 0.7 0.9	V V V V V V
$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \qquad 2.0$ $V_{IL} \qquad \text{LOW-level input voltage} \qquad V_{CC} = 0.8 \text{ V} \qquad -$ $V_{CC} = 0.9 \text{ V to } 1.95 \text{ V} \qquad -$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \qquad -$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \qquad -$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \qquad -$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \qquad -$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \qquad -$ $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \qquad -$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} \qquad -$ $I_{O} = -20 \text{ µA; } V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} \qquad V_{CC} = 0.1 \text{ V}$ $I_{O} = -1.1 \text{ mA; } V_{CC} = 1.1 \text{ V} \qquad 0.75 \times V_{CC} = 0.1 \text{ V}$ $I_{O} = -1.1 \text{ mA; } V_{CC} = 1.4 \text{ V} \qquad 1.11 \qquad -$ $I_{O} = -1.9 \text{ mA; } V_{CC} = 1.65 \text{ V} \qquad 1.32 \qquad -$ $I_{O} = -2.3 \text{ mA; } V_{CC} = 2.3 \text{ V} \qquad 1.9 \qquad -$ $I_{O} = -2.7 \text{ mA; } V_{CC} = 2.3 \text{ V} \qquad 2.05 \qquad -$ $I_{O} = -2.7 \text{ mA; } V_{CC} = 3.0 \text{ V} \qquad 2.72 \qquad -$ $I_{O} = -4.0 \text{ mA; } V_{CC} = 3.0 \text{ V} \qquad 2.6 \qquad -$ $V_{OL} \qquad \text{LOW-level output voltage} \qquad V_{I} = V_{IH} \text{ or } V_{IL} \qquad -$ $I_{O} = 20 \text{ µA; } V_{CC} = 1.4 \text{ V} \qquad -$ $I_{O} = 1.1 \text{ mA; } V_{CC} = 1.4 \text{ V} \qquad -$ $I_{O} = 1.7 \text{ mA; } V_{CC} = 1.4 \text{ V} \qquad -$ $I_{O} = 1.7 \text{ mA; } V_{CC} = 1.65 \text{ V} \qquad -$		- 0.30 × V _{CC} 0.35 × V _{CC} 0.7 0.9	V V V V V V
$\begin{array}{c} V_{IL} & LOW\mbox{-level input voltage} & V_{CC} = 0.8 \ V & - \\ \hline V_{CC} = 0.9 \ V \ to \ 1.95 \ V & - \\ \hline V_{CC} = 2.3 \ V \ to \ 2.7 \ V & - \\ \hline V_{CC} = 3.0 \ V \ to \ 3.6 \ V & - \\ \hline V_{OC} = 3.0 \ V \ to \ 3.6 \ V & - \\ \hline V_{OC} = 3.0 \ V \ to \ 3.6 \ V & V_{CC} = 0.1 \ V_{CC} $		0.35 × V _{CC} 0.7 0.9	V V V V V
$V_{CC} = 0.9 \text{ V to } 1.95 \text{ V} \\ V_{CC} = 2.3 \text{ V to } 2.7 \text{ V} \\ V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \\ V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \\ V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \\ V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} \\ V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} \\ V_{CC} = 0.1 $		0.35 × V _{CC} 0.7 0.9	V V V
$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V} \\ V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \\ V_{OH} \\ \hline $		0.7 0.9	V V
$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \\ V_{OH} \\ \hline \\ V_{OH} $		0.9	V
$\begin{array}{c} V_{OH} & \text{HIGH-level output voltage} \\ V_{I} = V_{IH} \text{ or } V_{IL} \\ \hline I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 0.8 \ V \text{ to } 3.6 \ V \\ \hline I_{O} = -1.1 \ \text{mA}; \ V_{CC} = 1.1 \ V \\ \hline I_{O} = -1.7 \ \text{mA}; \ V_{CC} = 1.4 \ V \\ \hline I_{O} = -1.9 \ \text{mA}; \ V_{CC} = 1.65 \ V \\ \hline I_{O} = -2.3 \ \text{mA}; \ V_{CC} = 1.65 \ V \\ \hline I_{O} = -2.3 \ \text{mA}; \ V_{CC} = 2.3 \ V \\ \hline I_{O} = -3.1 \ \text{mA}; \ V_{CC} = 2.3 \ V \\ \hline I_{O} = -2.7 \ \text{mA}; \ V_{CC} = 3.0 \ V \\ \hline I_{O} = -2.7 \ \text{mA}; \ V_{CC} = 3.0 \ V \\ \hline I_{O} = -4.0 \ \text{mA}; \ V_{CC} = 3.0 \ V \\ \hline V_{I} = V_{IH} \ \text{or } V_{IL} \\ \hline I_{O} = 20 \ \mu\text{A}; \ V_{CC} = 0.8 \ V \ \text{to } 3.6 \ V \\ \hline I_{O} = 1.1 \ \text{mA}; \ V_{CC} = 1.1 \ V \\ \hline I_{O} = 1.7 \ \text{mA}; \ V_{CC} = 1.4 \ V \\ \hline I_{O} = 1.9 \ \text{mA}; \ V_{CC} = 1.65 \ V \\ \hline \end{array}$		-	V
$\begin{array}{c} I_O = -20~\mu\text{A};~V_{CC} = 0.8~V~to~3.6~V~~V_{CC} - 0.1\\ I_O = -1.1~m\text{A};~V_{CC} = 1.1~V~~0.75 \times V_{CC}\\ I_O = -1.7~m\text{A};~V_{CC} = 1.4~V~~1.11\\ I_O = -1.9~m\text{A};~V_{CC} = 1.65~V~~1.32\\ I_O = -2.3~m\text{A};~V_{CC} = 2.3~V~~2.05\\ I_O = -3.1~m\text{A};~V_{CC} = 2.3~V~~1.9\\ I_O = -2.7~m\text{A};~V_{CC} = 3.0~V~~2.72\\ I_O = -4.0~m\text{A};~V_{CC} = 3.0~V~~2.6\\ \hline \\ V_{OL} & LOW\text{-level output voltage} & V_I = V_{IH}~or~V_{IL}\\ I_O = 20~\mu\text{A};~V_{CC} = 0.8~V~to~3.6~V~~-\\ I_O = 1.1~m\text{A};~V_{CC} = 1.4~V~~-\\ I_O = 1.7~m\text{A};~V_{CC} = 1.4~V~~-\\ I_O = 1.9~m\text{A};~V_{CC} = 1.65~V~~-\\ \hline \end{array}$		-	
$\begin{array}{c} I_O = -1.1 \text{ mA; } V_{CC} = 1.1 \text{ V} & 0.75 \times V_O \\ I_O = -1.7 \text{ mA; } V_{CC} = 1.4 \text{ V} & 1.11 \\ I_O = -1.9 \text{ mA; } V_{CC} = 1.65 \text{ V} & 1.32 \\ I_O = -2.3 \text{ mA; } V_{CC} = 2.3 \text{ V} & 2.05 \\ I_O = -3.1 \text{ mA; } V_{CC} = 2.3 \text{ V} & 1.9 \\ I_O = -2.7 \text{ mA; } V_{CC} = 3.0 \text{ V} & 2.72 \\ I_O = -4.0 \text{ mA; } V_{CC} = 3.0 \text{ V} & 2.6 \\ \end{array}$ $\begin{array}{c} V_{OL} & \text{LOW-level output voltage} & V_I = V_{IH} \text{ or } V_{IL} \\ I_O = 20 \mu\text{A; } V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} & -100 \\ I_O = 1.1 \text{ mA; } V_{CC} = 1.1 \text{ V} & -100 \\ I_O = 1.7 \text{ mA; } V_{CC} = 1.4 \text{ V} & -100 \\ I_O = 1.9 \text{ mA; } V_{CC} = 1.65 \text{ V} & -100 \\ \end{array}$		-	
$\begin{array}{c} I_O = -1.7 \text{ mA; } V_{CC} = 1.4 \text{ V} & 1.11 \\ I_O = -1.9 \text{ mA; } V_{CC} = 1.65 \text{ V} & 1.32 \\ I_O = -2.3 \text{ mA; } V_{CC} = 2.3 \text{ V} & 2.05 \\ I_O = -3.1 \text{ mA; } V_{CC} = 2.3 \text{ V} & 1.9 \\ I_O = -2.7 \text{ mA; } V_{CC} = 3.0 \text{ V} & 2.72 \\ I_O = -4.0 \text{ mA; } V_{CC} = 3.0 \text{ V} & 2.6 \\ \end{array}$ $\begin{array}{c} V_{OL} & \text{LOW-level output voltage} & V_I = V_{IH} \text{ or } V_{IL} \\ I_O = 20 \mu\text{A; } V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} & -1.00 \\ I_O = 1.1 \text{ mA; } V_{CC} = 1.1 \text{ V} & -1.00 \\ I_O = 1.7 \text{ mA; } V_{CC} = 1.4 \text{ V} & -1.00 \\ I_O = 1.9 \text{ mA; } V_{CC} = 1.65 \text{ V} & -1.00 \\ \end{array}$	C - -	-	
$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V} \qquad \qquad 1.32$ $I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V} \qquad \qquad 2.05$ $I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V} \qquad \qquad 1.9$ $I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V} \qquad \qquad 2.72$ $I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V} \qquad \qquad 2.6$ $V_{OL} \qquad \qquad V_{I} = V_{IH} \text{ or } V_{IL}$ $I_{O} = 20 \mu\text{A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} \qquad \qquad -$ $I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V} \qquad \qquad -$ $I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V} \qquad \qquad -$ $I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V} \qquad \qquad -$	-		V
$\begin{array}{c} I_O = -2.3 \text{ mA; } V_{CC} = 2.3 \text{ V} & 2.05 \\ I_O = -3.1 \text{ mA; } V_{CC} = 2.3 \text{ V} & 1.9 \\ I_O = -2.7 \text{ mA; } V_{CC} = 3.0 \text{ V} & 2.72 \\ I_O = -4.0 \text{ mA; } V_{CC} = 3.0 \text{ V} & 2.6 \\ \end{array}$ $\begin{array}{c} V_{OL} & \text{LOW-level output voltage} & V_I = V_{IH} \text{ or } V_{IL} \\ I_O = 20 \mu\text{A; } V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} & - \\ I_O = 1.1 \text{ mA; } V_{CC} = 1.1 \text{ V} & - \\ I_O = 1.7 \text{ mA; } V_{CC} = 1.4 \text{ V} & - \\ I_O = 1.9 \text{ mA; } V_{CC} = 1.65 \text{ V} & - \\ \end{array}$	_	-	V
$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V} \qquad \qquad 1.9$ $I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V} \qquad \qquad 2.72$ $I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V} \qquad \qquad 2.6$ $V_{OL} \qquad \qquad V_{I} = V_{IH} \text{ or } V_{IL}$ $I_{O} = 20 \mu\text{A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} \qquad \qquad -$ $I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V} \qquad \qquad -$ $I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V} \qquad \qquad -$ $I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V} \qquad \qquad -$		-	V
$I_O = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V} \qquad 2.72$ $I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V} \qquad 2.6$ $V_{OL} \qquad \text{LOW-level output voltage} \qquad V_I = V_{IH} \text{ or } V_{IL}$ $I_O = 20 \mu\text{A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} \qquad -$ $I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V} \qquad -$ $I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V} \qquad -$ $I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V} \qquad -$	-	-	V
$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V} \qquad 2.6$ $V_{OL} \qquad \text{LOW-level output voltage} \qquad V_{I} = V_{IH} \text{ or } V_{IL}$ $I_{O} = 20 \mu\text{A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V} \qquad -$ $I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V} \qquad -$ $I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V} \qquad -$ $I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V} \qquad -$	-	-	V
V _{OL} LOW-level output voltage $\begin{aligned} V_I &= V_{IH} \text{ or } V_{IL} \\ I_O &= 20 \ \mu\text{A}; \ V_{CC} = 0.8 \ \text{V to } 3.6 \ \text{V} \end{aligned} \\ I_O &= 1.1 \ \text{mA}; \ V_{CC} = 1.1 \ \text{V} \\ I_O &= 1.7 \ \text{mA}; \ V_{CC} = 1.4 \ \text{V} \end{aligned} \\ I_O &= 1.9 \ \text{mA}; \ V_{CC} = 1.65 \ \text{V} \end{aligned}$	-	-	V
$I_{O} = 20 \; \mu \text{A}; \; V_{CC} = 0.8 \; \text{V to } 3.6 \; \text{V}$ $I_{O} = 1.1 \; \text{mA}; \; V_{CC} = 1.1 \; \text{V}$ $I_{O} = 1.7 \; \text{mA}; \; V_{CC} = 1.4 \; \text{V}$ $I_{O} = 1.9 \; \text{mA}; \; V_{CC} = 1.65 \; \text{V}$	-	-	V
I_{O} = 1.1 mA; V_{CC} = 1.1 V - I_{O} = 1.7 mA; V_{CC} = 1.4 V - I_{O} = 1.9 mA; V_{CC} = 1.65 V -			
$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$ - $I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$ -	-	0.1	V
$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	$0.3\times V_{\text{CC}}$	V
	-	0.31	V
$I_{\rm O} = 2.3 \text{mA}; V_{\rm CC} = 2.3 \text{V}$	-	0.31	V
, , ,	-	0.31	V
$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	0.44	V
$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.31	V
$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	0.44	V
input leakage current $V_1 = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	±0.1	μΑ
OFF power-off leakage current V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	±0.2	μΑ
ΔI_{OFF} additional power-off V_{I} or $V_{O} = 0$ V to 3.6 V; - leakage current $V_{CC} = 0$ V to 0.2 V	-	±0.2	μΑ
supply current $V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A}; V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	0.5	μΑ
additional supply current $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	40	μΑ
$V_{CC} = 0 \text{ V to } 3.6 \text{ V; } V_{I} = \text{GND or } V_{CC}$	8.0	-	рF
$V_{O} = V_{O} = 0$ output capacitance $V_{O} = 0$ output capacitance $V_{O} = 0$	1.7	-	pF

Low-power dual 2-input NAND gate

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V}$	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.30 \times V_{\text{CC}}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	٧
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	٧
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH}$ or V_{IL}				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		$I_O = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	٧
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	٧
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
OFF	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
Δl _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μΑ
CC	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μΑ
Δl _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1] -	-	50	μΑ

Low-power dual 2-input NAND gate

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.75 \times V_{CC}$	-	-	٧
		V _{CC} = 0.9 V to 1.95 V	$0.70 \times V_{\text{CC}}$	-	-	٧
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	٧
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	٧
/ _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.25 \times V_{CC}$	٧
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.30 \times V_{CC}$	٧
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	٧
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	٧
/ _{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	V _{CC} – 0.11	-	-	٧
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	٧
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	٧
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	٧
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	٧
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	٧
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	٧
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	٧
/ _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	٧
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.33 \times V_{CC}$	٧
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	٧
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	٧
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	٧
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	٧
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
OFF	power-off leakage current	V_{I} or $V_{O} = 0 \text{ V}$ to 3.6 V; $V_{CC} = 0 \text{ V}$	-	-	±0.75	μΑ
N _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μA
CC	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μΑ
VI _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	[1] -	-	75	μΑ

^[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

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11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol Parameter Conditions			Tai	_{mb} = 25	°C	T _{amb} =	–40 °C to	+125 °C	Unit	
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 p$	F									'
t _{pd}	propagation delay	nA, nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	17.5	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.5	5.3	11.0	2.1	12.2	13.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.0	3.8	6.8	1.8	7.8	8.6	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.6	3.1	5.3	1.4	6.2	6.9	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.3	2.5	4.0	1.1	4.7	5.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	2.2	3.6	1.0	4.2	4.7	ns
C _L = 10	pF									
t_{pd}	propagation delay	nA, nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	21.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.4	6.1	13.0	2.2	14.4	15.9	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.4	4.4	7.9	2.2	9.2	10.2	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.0	3.7	6.2	1.9	7.3	8.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.4	3.0	4.7	1.3	5.6	6.2	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.3	2.8	4.3	1.2	4.9	5.4	ns
C _L = 15	pF									
t_{pd}	propagation delay	nA, nB to nY; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	24.5	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.4	6.9	14.8	3.1	16.5	18.2	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.8	5.0	8.9	2.5	10.5	11.6	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.0	4.1	7.0	2.0	8.3	9.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.7	3.5	5.3	1.5	6.4	7.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.6	3.2	4.9	1.4	5.7	6.3	ns
C _L = 30	pF									
t_{pd}	propagation delay		[2]							
		$V_{CC} = 0.8 \text{ V}$		-	34.8	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		4.6	9.2	20.1	4.1	22.6	24.9	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		3.0	6.5	11.8	2.9	14.0	15.4	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.6	5.4	9.3	2.3	11.1	12.3	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.4	4.6	7.1	2.1	8.5	9.4	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.3	4.3	6.5	2.1	7.6	8.4	ns

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Dynamic characteristics ...continued Table 8.

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	T _{amb} = 25 °C		T _{amb} = -40 °C to +125 °C			Unit		
			Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)		
$C_L = 5 pl$	F, 10 pF, 15 pF and	30 pF								
C_{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	[3]							
		$V_{CC} = 0.8 \text{ V}$		-	2.8	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	2.9	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	3.0	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	3.0	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	3.4	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	3.9	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

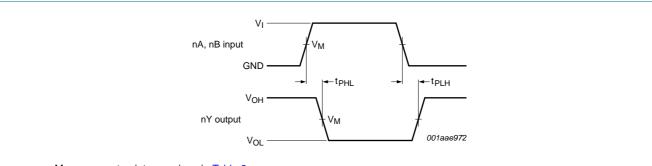
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

12. Waveforms



Measurement points are given in Table 9.

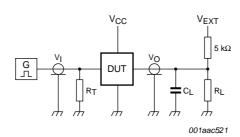
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

The data input (nA or nB) to output (nY) propagation delays Fig 8.

Measurement points Table 9.

Supply voltage	Output	Input						
V _{CC}	V _M	V _M	VI	$t_r = t_f$				
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{CC}	≤ 3.0 ns				

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Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V _{EXT}		
V _{CC}	C _L	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

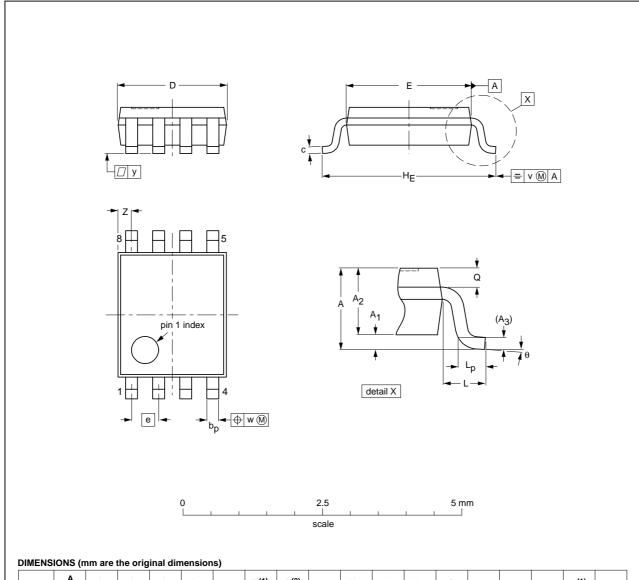
[1] For measuring enable and disable times R_L = 5 k Ω .

For measuring propagation delays, setup and hold times and pulse width R_L = 1 $M\Omega$.

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT765-1		MO-187				02-06-07

Fig 10. Package outline SOT765-1 (VSSOP8)

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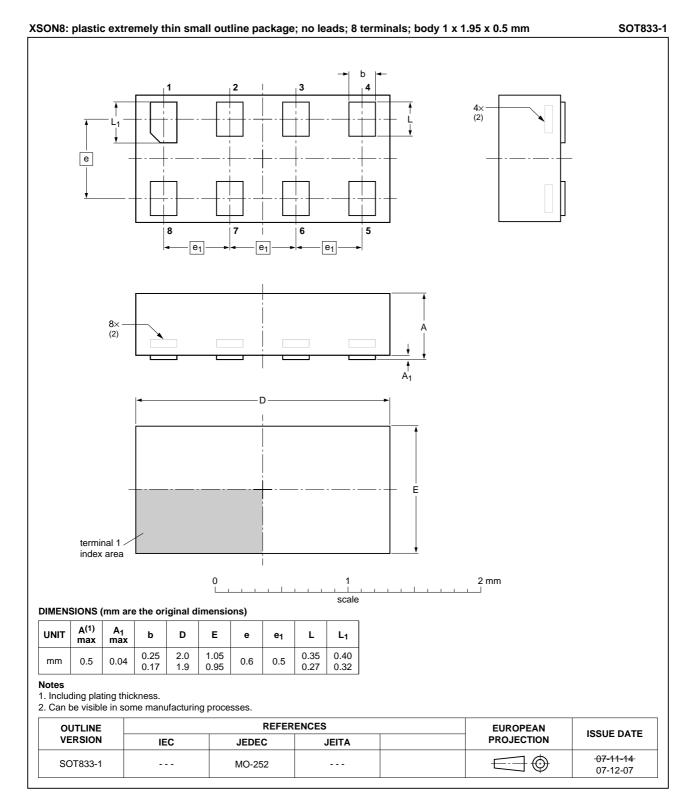


Fig 11. Package outline SOT833-1 (XSON8)

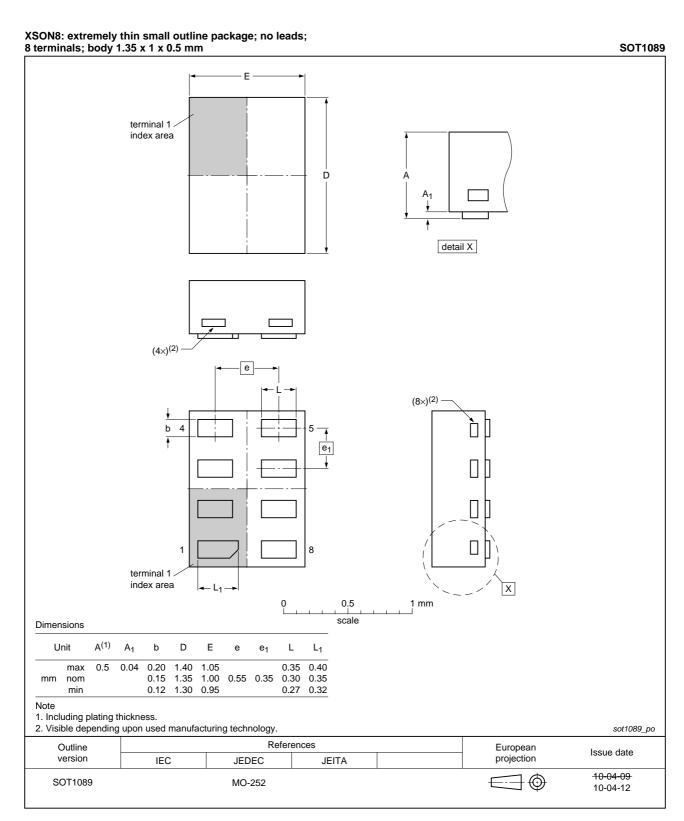


Fig 12. Package outline SOT1089 (XSON8)

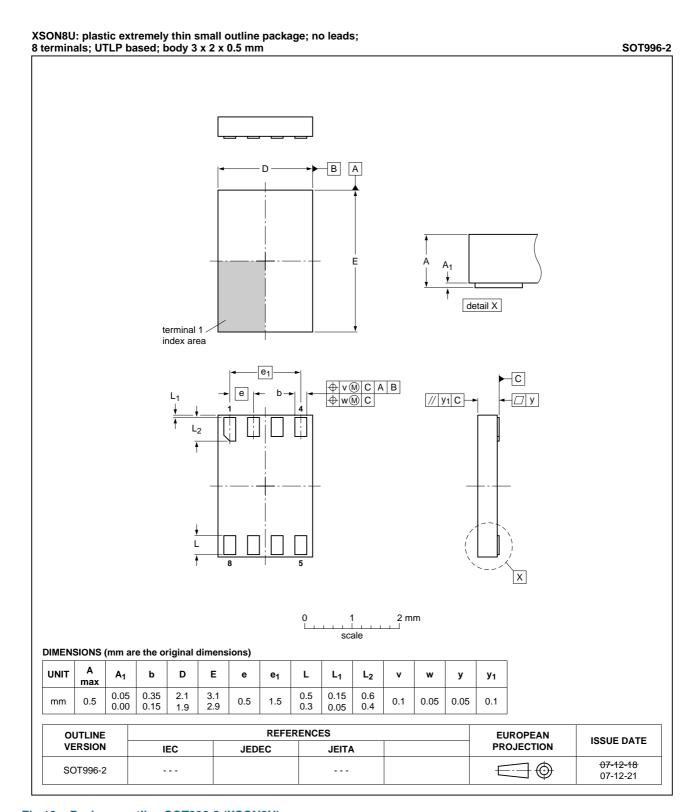


Fig 13. Package outline SOT996-2 (XSON8U)

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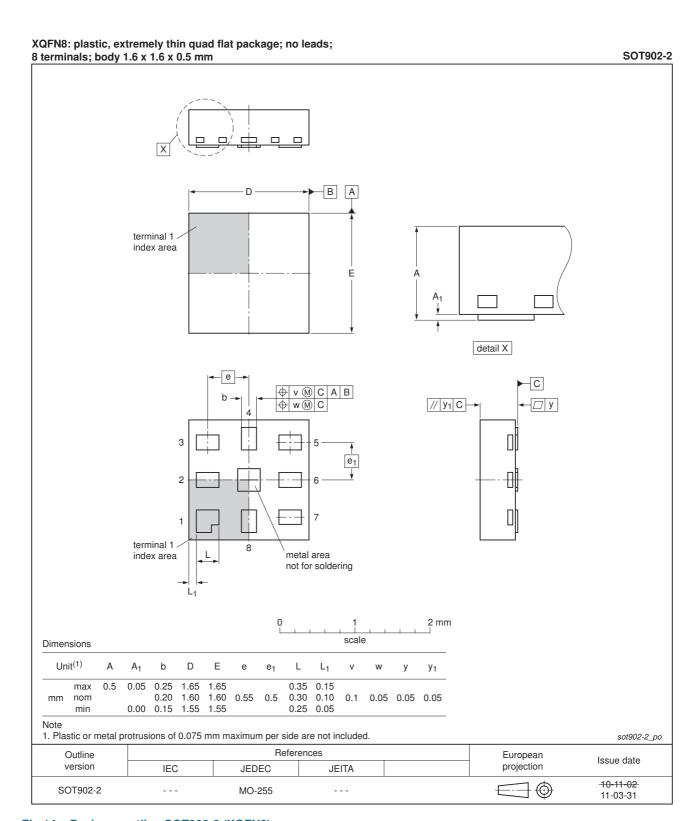


Fig 14. Package outline SOT902-2 (XQFN8)

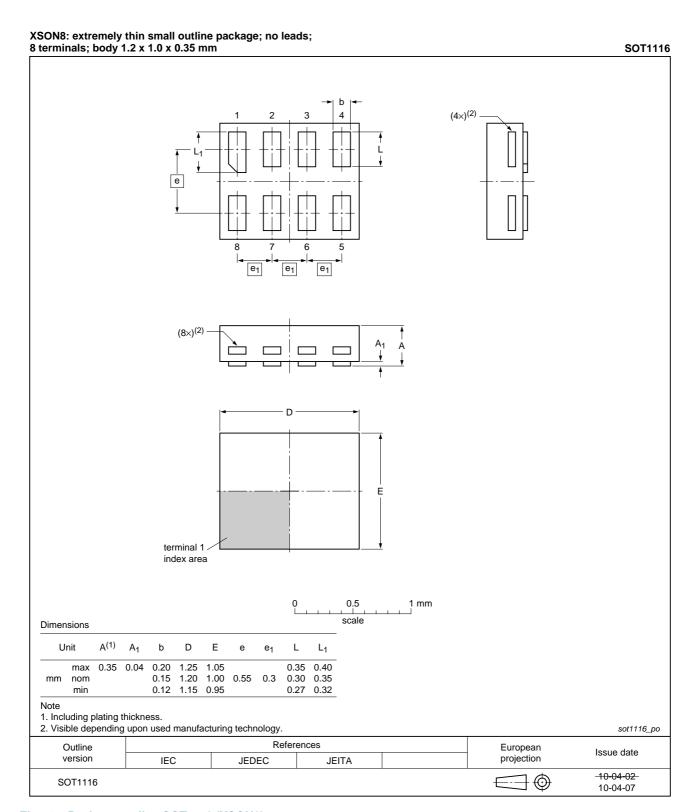


Fig 15. Package outline SOT1116 (XSON8)

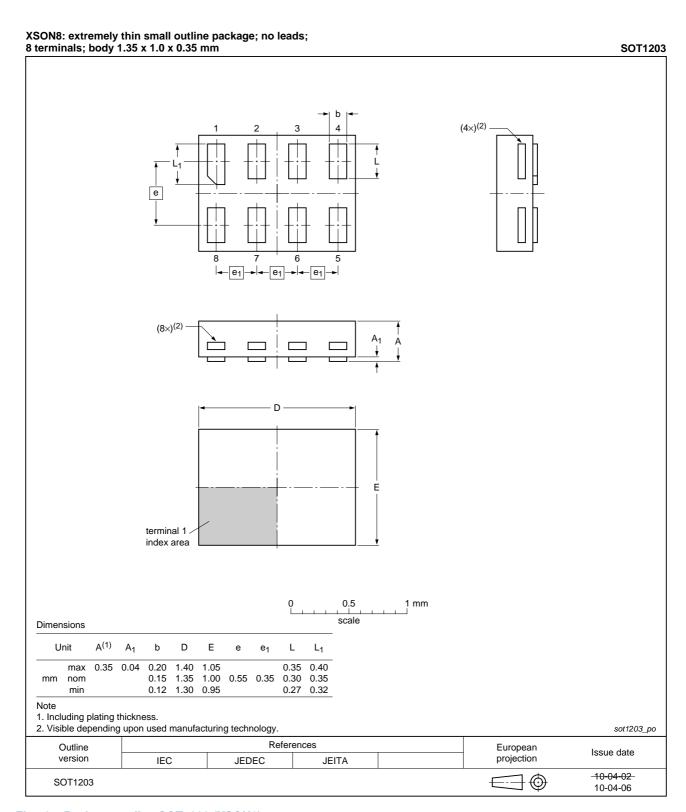


Fig 16. Package outline SOT1203 (XSON8)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G00 v.7	20120608	Product data sheet	-	74AUP2G00 v.6
Modifications:	 For type num 	nber 74AUP2G00GM the SOT	code has changed to SOTS	902-2.
74AUP2G00 v.6	20111201	Product data sheet	-	74AUP2G00 v.5
Modifications:	 Legal pages 	updated.		
74AUP2G00 v.5	20101021	Product data sheet	-	74AUP2G00 v.4
74AUP2G00 v.4	20080605	Product data sheet	-	74AUP2G00 v.3
74AUP2G00 v.3	20080403	Product data sheet	-	74AUP2G00 v.2
74AUP2G00 v.2	20070515	Product data sheet	-	74AUP2G00 v.1
74AUP2G00 v.1	20060825	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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